

OSZ-1017B-7V

SILICON BIDIRECTIONAL ZENER DIODE

ASYMMETRY TYPE BIDIRECTIONAL ZENER DIODE

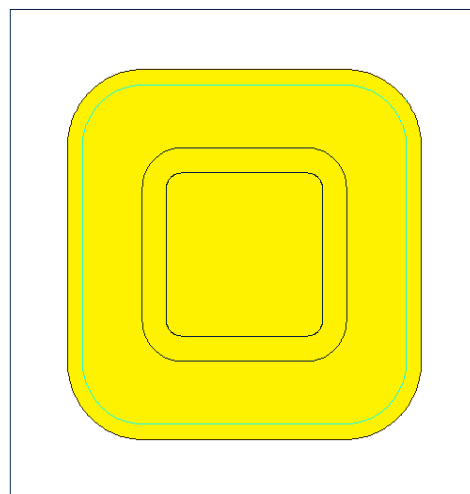
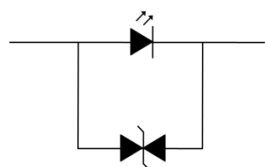
TENTATIVE

APPLICATION : Surge ESD Protector

- DIE SIZE $0.150(\pm 0.02)\text{mm} \times 0.150(\pm 0.02)\text{mm}$
- DIE THICKNESS $100\mu\text{m} \pm 20\mu\text{m}$
- METALLIZATION
 - TOP Au
 - BOTTOM Au

- BONDING PAD SIZE
 - TOP ELECTRODE $115\mu\text{m} \times 115\mu\text{m}$
 - BOTTOM ELECTRODE

• SCHEMATIC DIAGRAM

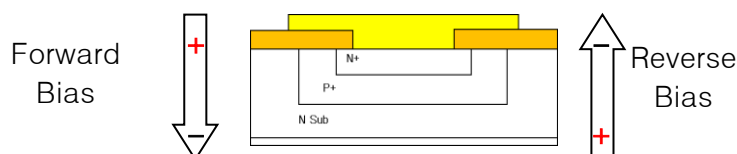


- ANNOTATION :
 - Parallel with one LED
 - Single pad (one wire bonding applied only)
 - Double direction Zener

• ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Zener Voltage	$V_{Z(R)}$	$I_Z=5\text{mA}$	6.0		9.0	V
Forward Zener Voltage	$V_{Z(F)}$	$I_F=5\text{mA}$	4.5		7.5	V
Reverse Current	I_R	$V_R=3.5\text{V}$			0.1	μA
Forward Current	I_F	$V_F=3.5\text{V}$			0.1	μA

• THE DIRECTION OF BIAS IS USED TO ELECTRICAL CHARACTERISTICS TEST



• ABSOLUT MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Maximum Rating	Unit
Power Dissipation	P_d	30	mW
Junction Temperature	T_J	150	$^\circ\text{C}$

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PART NAME : BIDIRECTIONAL ZENER DIODE

PART NUMBER : OSZ-1017B-7V

